

2823  
71

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLN. OF: ASPAR et al.  
SERIAL NO.: 09/777,516  
FILED: February 6, 2001  
FOR: A Method of Producing a Thin Layer of Semiconductor Material  
GROUP: 2823  
EXAMINER: FOURSON III, GEORGE  
DOCKET: BREV 12370 CON3

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Dear Sir:

In connection with the above-entitled matter, Applicants hereby proffer U.S. Patent Office Form PTO-1449, including copies of the references listed therein. These references came to applicants' attention in connection with litigation concerning a related U.S. Patent. The claims in the present application are believed to be patentably distinguished over these references.

This Supplemental Information Disclosure Statement is being made pursuant to the duty of disclosure imposed by law and formulated in 37 CFR 1.56(A). No representation is made that the information thus disclosed in fact constitutes prior art or that it is the closest prior art, inasmuch as 37 CFR 1.56(A) relies on a materiality concept which depends on subjectivity.


This Supplemental Information Disclosure Statement is being filed prior to the issuance of a further action following the filing of the Request for Continuation of Examination.

HAYES SOLOWAY P.C.  
130 W. CUSHING ST.  
TUCSON, AZ 85701  
TEL. 520.882.7623  
FAX. 520.882.7643

175 CANAL STREET  
MANCHESTER, NH 03101  
TEL. 603.668.1400  
FAX. 603.668.8567

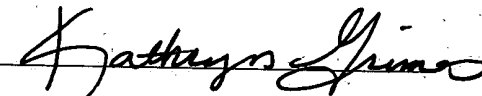
Therefore, we believe there are no fees involved with this Information Disclosure Statement. In the event there are additional fees payable, please charge them to our Deposit Account No. 08-1391.

Respectfully submitted,

  
Norman P. Soloway  
Attorney for Applicants  
Reg. No. 24,315

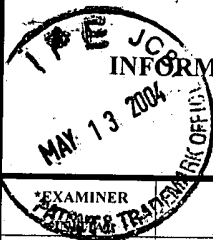
CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on May 10, 2004 at Tucson, Arizona.

By: 

HAYES SOLOWAY P.C.  
130 W. CUSHING ST.,  
TUCSON, AZ 85701  
TEL. 520.882.7623  
FAX. 520.882.7643

175 CANAL STREET  
MANCHESTER, NH 03101  
TEL. 603.668.1400  
FAX. 603.668.8567



## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

BREV 12370 CON3

Application Number

09/777,516

Applicant(s)

ASPAR et al.

Filing Date

February 6, 2001

Group Art Unit

2823

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

"Hydrogen-Related Complexes as the Stressing Species in High-Fluence, Hydrogen-Implanted, Single-Crystal Silicon" Cerofolini et al., *Physical Review B*, Volume 46, Number 4, 1992, pgs. 2061-2070

"Crystallographic Nature and Formation Mechanisms of Highly Irregular Structure in Implanted and Annealed Si Layers" Komarov et al., *Radiation Effects*, Volume 42, 1979, pgs. 169-178

"Observation of Blistering and Amorphization on Germanium Surface After 450 keV Ar+ION Bombardment" Kamada et al., *Radiation Effects*, Volume 28, 1976, pgs. 43-48

"Orientation Dependence of Flaking of Ion Irradiated Aluminum Single Crystals" Ono et al., *Japanese Journal of Applied Physics*, Volume 25, No., 10, 1986, pgs. 1475-1480

"High Fluence Retention of Noble Gases Implanted in Silicon" Wittmaack et al., *Radiation Effects*, Volume 39, 1978, pgs. 81-95

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.